

Taiwan Semiconductor Co. Ltd. 11Fl., No. 205, Sec. 3, Beishin Rd. Xindian Dist., New Taipei City 231 Taiwan. R.O.C.

> Tel.:+886 2 8913 1588 Fax: +886 2 8913 1788 www.taiwansemi.com

# **Process Change Notification**

This is to inform you that a design and/or process change/s will be implemented to the following product(s) listed below. This notification requires your concurrence within 45 days upon receipt of this notification.

The plan change/s will take effect 90 calendar days from the date of this notification.

Please work with your local Taiwan Semiconductor Sales Representative to manage your inventory of the existing product if your evaluation of this change will require more than 90 calendar days.

For additional data and samples, you can contact your local Taiwan Semiconductor Field Quality Service or Customer Quality Engineer within 45 days upon receipt of this notification

PCN No: PCN23006 rev0

Title: 200V UG Series TO-3P Additional Wafer Source

Issue Date: 2023/6/2

If you have any questions concerning this change, please contact:

#### **PCN** Coordinator

Name: Sunnie Lin

E-Mail: sunnie.lin@mail.ts.com.tw Phone: +886 8913 1588 ext. 2205

#### **PCN Originator**

Name: Daisy Liang

E-mail: daisy@mail.tsyew.com.cn Phone: +86 5438691091 ext. 3108

# Reliability Engineer

Name: Roben Jiao

E-mail: roben@mail.tsyew.com.cn Phone: +86 5438691091 ext. 3110

**PCN Type:** Additional Wafer Source

Effectivity:

Expected 1st device shipment date: 2023/8/31

# **Product Category (Description):**

200V Ultra Fast Rectifier in TO-3P package. See detailed part numbers in the List of Affected Devices.

## **Description of Change:**

This change notification is being issued to notify customer that in order to assure continuity of supply, Taiwan Semiconductor Company is qualifying its own wafer fabrication located in Li-je for 200V, Ultra Fast Rectifier assembled in TO-3P package.

Full electrical characterization and high reliability testing has been completed on the representative devices to ensure no change to the device functionality or electrical specifications in the datasheet.

Wafer Structure Comparison:

Walet Chactare Companion.				
Item	Current	Additional	Remarks	
Die Source	Silan	Lije	Add second source	
Wafer Diameter	5"	6"	Larger wafer diameter	
Top/Back Metal Layer	Ti-Ni-Ag	Al-Ti-Ni-Ag	Different metal layer	
Die Passivation	Polyimide	SiO <sub>2</sub> /Polyimide	Different passivation material	
Die size	98mil	98mil	Same die size	
Die thickness	280µm	280µm	Same die thickness	

Remarks: No major differences that can affect product quality and reliability. No expected impact to the product functionality (form, fit and function).

#### **Qualification Results:**

Qual Vehicle: PU1DLSH (1 lot), UG54G (1 lot), UG1004G (1 lot), UG2004PT (1 lot) Qualification/Reliability Result (AECQ-101)

Item	Test Condition / Duration	Reference Standard	#lot	Sample Size	Remarks
Pre- and Post- Stress Electrical Test	Electrical characteristic @25°C	Data sheet	4	540*1 555*3	Pass
Pre-conditioning <sup>①</sup>	Bake:125°C 24hrs Soak:85°C RH:85% 168hrs IR Reflow: Tpeak=245± 5°C 3cycles	JESD22A-113	1	308*1	Pass

Item	Test Condition / Duration	Reference Standard	#lot	Sample Size	Remarks
EV (External Visual)	Inspect part construction and marking, per TSC Spec.	JESD22B-101	4	540*1 555*3	Pass
PV (Parameter Verification)	Electrical characterization @-55/25/150°C	Data sheet	4	30*4	Pass
HTRB (High Temperature Reverse Bias)	100% Rated VR (Tj=175° C) / 1008hrs	MIL-STD-750 Method 1038	4	77*1 80*3	Pass
TC (Temp. Cycling)	150°C(+15,-0)/15mins, - 55°C(-10,+0)/15mins, 1016 cycles	JESD22A-104 Appendix 6	4	77*1 80*3	Pass
UHAST (Unbiased Highly Accelerated Stress Test)	Ta=130°C, 85% RH/ 96hrs	JESD22-A118	4	77*1 80*3	Pass
HAST (Highly Accelerated Stress Test)	Ta=110°C, 85% RH 80% rated VR up to 42Vmax /264H	JESD22-A110	4	77*1 80*3	Pass
IOL (Intermittent Operational Life)	For PU1DLSH&UG54G: On/ 2mins, Off/ 2mins, $\Delta$ Tj $\geq$ 100°C, 15120cycles For UG1004G: On/ 3.5mins, Off/ 3.5mins, $\Delta$ Tj $\geq$ 100°C, 8640cycles For UG2004PT: On/ 5mins, Off/ 5mins, $\Delta$ Tj $\geq$ 100°C, 6048cycles	MIL-STD-750 Method 1037 AEC-Q101 Table 2A	4	77*1 80*3	Pass
ESD (IEC)	Contact: (C=150pf R:330 $\Omega$ )/ 10Pulses	IEC-61000-4-2	4	15*4	Pass
ESD HBM	HBM: (C=100pf R:1500 Ω)/ 6Pulses	AEC-Q101-001	4	30*4	8KV/H3B
ESD CDM	CDM: (Field induced charge)/ 6Pulses	AEC-Q101-005	4	30*4	>1KV/C5
DPA (Destructive Physical Analysis)	TC passed chose 2pcs of the 1 lot HAST or HTRB passed chose 2pcs of the 1 lot	AEC-Q101-004	4	4*4	Pass

Item	Test Condition / Duration	Reference Standard	#lot	Sample Size	Remarks
RSH (Resist.to Solder Heat)	Ta=260±5°C/ 10secs	JESD22- A111 (SMD)	4	30*4	Pass
TR (Thermal Resistance)	Per. TSC Spec.	JESD24-3, 24- 4, 24-6 as appropriate	4	10*4	Pass

Note: 1 Pre-conditioning only available for SMD series product.

**Conclusion:** The product passed the full reliability required in AECQ101 standard.

## Identification and Traceability:

Item	Identification
Traceability	Product date code

## **Effect of Change:**

There is no impact in product Form, Fit and Function. This change will guarantee Taiwan Semiconductor commitment on customer service and satisfaction through continuous improvement.

## **List of Affected Devices:**

Family	Package	Ordering Code
20A, 200V Ultra Fast Rectifier	TO-247AD (TO-3P)	UG2004PT
20A, 200V Ultra Fast Rectifier	TO-247AD (TO-3P)	UG2004PTH